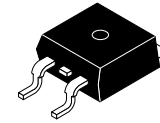


ECOSPARK[®] Ignition IGBT

500 mJ, 450 V, N-Channel Ignition IGBT

ISL9V5045S3ST-F085C



D²PAK-3
CASE 418AJ

Features

- SCIS Energy = 500 mJ at $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Automotive Ignition Coil Driver Circuits
- High Current Ignition System
- Coil on Plug Applications

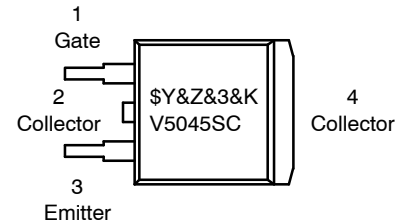
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Collector to Emitter Breakdown Voltage ($I_C = 1\text{ mA}$)	BV_{CER}	480	V
Emitter to Collector Voltage – Reverse Battery Condition ($I_C = 10\text{ mA}$)	BV_{ECS}	24	V
$I_{SCIS} = 39.2\text{ A}$, $L = 650\text{ }\mu\text{H}$, $R_{GE} = 1\text{ k}\Omega$, $T_C = 25^\circ\text{C}$ (Note 1)	$ESCIS_{25}$	500	mJ
$I_{SCIS} = 31.1\text{ A}$, $L = 650\text{ }\mu\text{H}$, $R_{GE} = 1\text{ k}\Omega$, $T_C = 150^\circ\text{C}$ (Note 2)	$ESCIS_{150}$	315	mJ
Collector Current Continuous, at $V_{GE} = 4.0\text{ V}$, $T_C = 25^\circ\text{C}$	IC_{25}	51	A
Collector Current Continuous, at $V_{GE} = 4.0\text{ V}$, $T_C = 110^\circ\text{C}$	IC_{110}	43	A
Gate to Emitter Voltage Continuous	V_{GEM}	± 10	V
Power Dissipation Total, $T_C = 25^\circ\text{C}$	PD	300	W
Power Dissipation Derating, $T_C > 25^\circ\text{C}$	PD	2	W/ $^\circ\text{C}$
Operating Junction and Storage Temperature	T_J, T_{STG}	-40 to 175	$^\circ\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	300	$^\circ\text{C}$
Reflow soldering according to JESD020C	T_{PKG}	260	$^\circ\text{C}$
HBM–Electrostatic Discharge Voltage at 100 pF, 1500 Ω	ESD	4	kV
CDM–Electrostatic Discharge Voltage at 1 Ω	ESD	2	kV

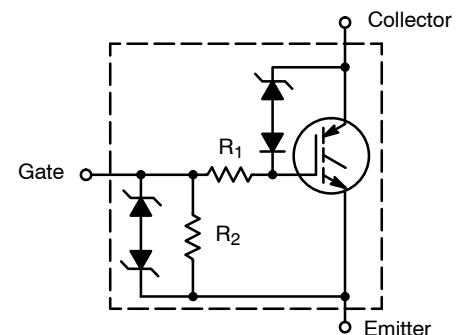
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Self Clamped inductive Switching Energy ($ESCIS_{25}$) of 500 mJ is based on the test conditions that is starting $T_J = 25^\circ\text{C}$, $L = 650\text{ }\mu\text{H}$, $I_{SCIS} = 39.2\text{ A}$, $V_{CC} = 100\text{ V}$ during inductor charging and $V_{CC} = 0\text{ V}$ during time in clamp.
2. Self Clamped inductive Switching Energy ($ESCIS_{150}$) of 315 mJ is based on the test conditions that is starting $T_J = 150^\circ\text{C}$, $L = 650\text{ }\mu\text{H}$, $I_{SCIS} = 31.1\text{ A}$, $V_{CC} = 100\text{ V}$ during inductor charging and $V_{CC} = 0\text{ V}$ during time in clamp.

MARKING DIAGRAM



$\$Y$ = ON Semiconductor Logo
 $\&Z$ = Assembly Plant Code
 $\&3$ = Date Code (Week & Year)
 $\&K$ = Lot Code
 $V5045SC$ = Specific Device Code



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ISL9V5045S3ST-F085C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Drain)	$R_{\theta JC}$	0.9	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector to Emitter Breakdown Voltage	BV_{CER}	$I_{CE} = 2\text{ mA}$, $V_{GE} = 0\text{ V}$, $R_{GE} = 1\text{ k}\Omega$, $T_J = -40\text{ to }150^\circ\text{C}$		420	450	480	V
Collector to Emitter Breakdown Voltage	BV_{CES}	$I_{CE} = 10\text{ mA}$, $V_{GE} = 0\text{ V}$, $R_{GE} = 0\text{ }\Omega$, $T_J = -40\text{ to }150^\circ\text{C}$		445	475	505	V
Emitter to Collector Breakdown Voltage	BV_{ECS}	$I_{CE} = -75\text{ mA}$, $V_{GE} = 0\text{ V}$, $T_J = 25^\circ\text{C}$		30	–	–	V
Gate to Emitter Breakdown Voltage	BV_{GES}	$I_{GES} = \pm 2\text{ mA}$		± 12	± 14	–	V
Collector to Emitter Leakage Current	I_{CER}	$V_{CE} = 175\text{ V}$, $R_{GE} = 1\text{ k}\Omega$	$T_J = 25^\circ\text{C}$	–	–	25	μA
			$T_J = 150^\circ\text{C}$	–	–	1	mA
Emitter to Collector Leakage Current	I_{ECS}	$V_{EC} = 24\text{ V}$	$T_J = 25^\circ\text{C}$	–	–	1	mA
			$T_J = 150^\circ\text{C}$	–	–	40	mA
Series Gate Resistance	R_1			–	100	–	Ω
Gate to Emitter Resistance	R_2			10	–	30	k Ω

ON CHARACTERISTICS

Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_{CE} = 10\text{ A}$, $V_{GE} = 4.0\text{ V}$, $T_J = 25^\circ\text{C}$		–	1.25	1.6	V
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_{CE} = 15\text{ A}$, $V_{GE} = 4.5\text{ V}$, $T_J = 150^\circ\text{C}$		–	1.47	1.8	V

DYNAMIC CHARACTERISTICS

Gate Charge	$Q_{G(ON)}$	$I_{CE} = 10\text{ A}$, $V_{CE} = 12\text{ V}$, $V_{GE} = 5\text{ V}$		–	32	–	nC
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	$I_{CE} = 1\text{ mA}$, $V_{CE} = V_{GE}$	$T_J = 25^\circ\text{C}$	1.3	–	2.2	V
			$T_J = 150^\circ\text{C}$	0.75	–	1.8	V
Gate to Emitter Plateau Voltage	V_{GEP}	$V_{CE} = 12\text{ V}$, $I_{CE} = 12\text{ A}$		–	3.1	–	V

SWITCHING CHARACTERISTICS

Current Turn-On Delay Time-Resistive	$td_{(ON)R}$	$V_{CE} = 14\text{ V}$, $R_L = 1\text{ }\Omega$, $V_{GE} = 5\text{ V}$, $R_G = 1\text{ k}\Omega$, $T_J = 25^\circ\text{C}$	–	0.7	4	μs
Current Rise Time-Resistive	t_{rR}		–	2.1	7	
Current Turn-Off Delay Time-Inductive	$td_{(OFF)L}$	$V_{CE} = 300\text{ V}$, $L = 650\text{ }\mu\text{H}$, $V_{GE} = 5\text{ V}$, $R_G = 1\text{ k}\Omega$, $T_J = 25^\circ\text{C}$	–	10.8	15	
Current Fall Time-Inductive	t_{fL}		–	2.8	15	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
ISL9V5045S3ST-F085C	D ² PAK-3 (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

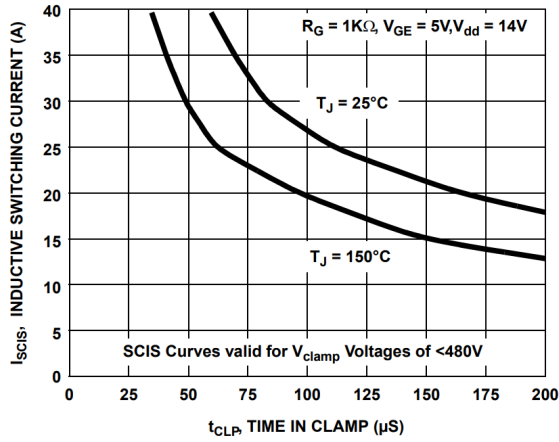


Figure 1. Self Clamped Inductive Switching Current vs. Time in Clamp

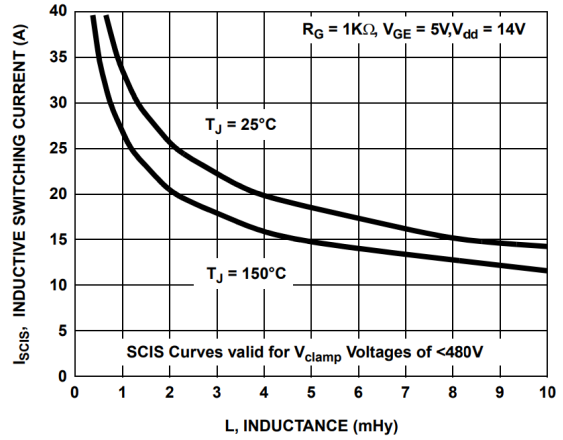


Figure 2. Self Clamped Inductive Switching Current vs. Inductance

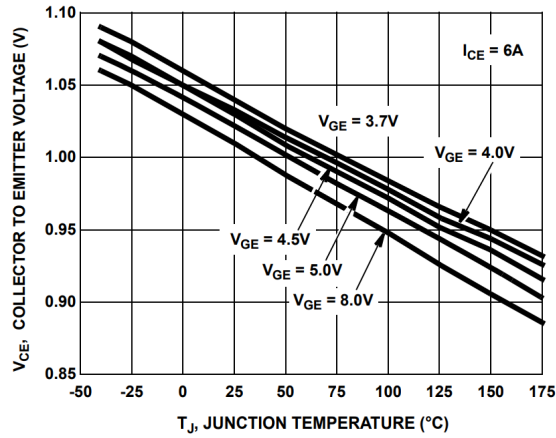


Figure 3. Collector to Emitter On-State Voltage vs. Junction Temperature

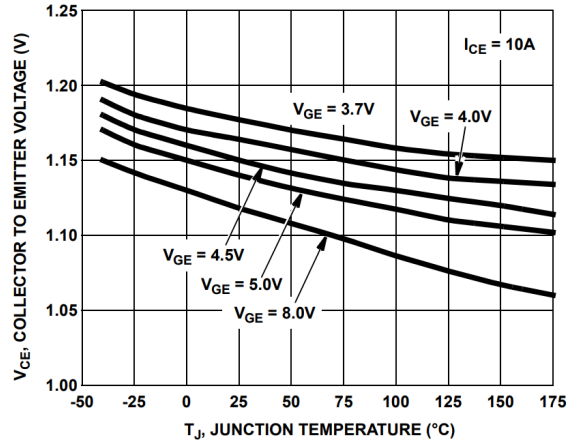


Figure 4. Collector to Emitter On-State Voltage vs. Junction Temperature

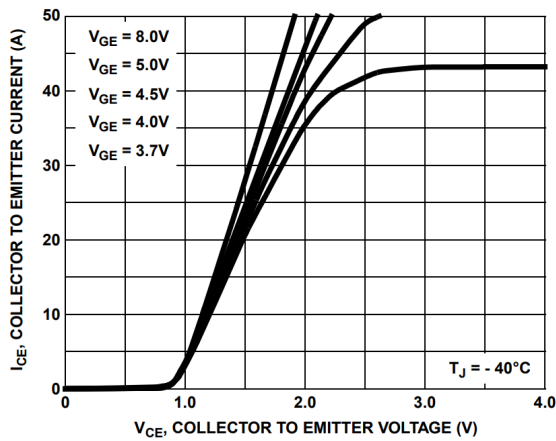


Figure 5. Collector to Emitter On-State Voltage vs. Collector Current

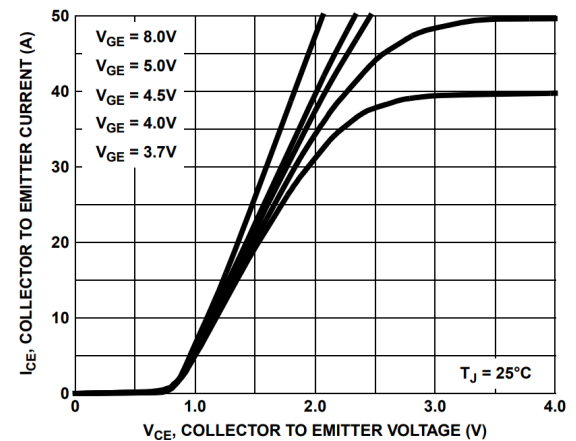


Figure 6. Collector to Emitter On-State Voltage vs. Collector Current

TYPICAL CHARACTERISTICS (Continued)

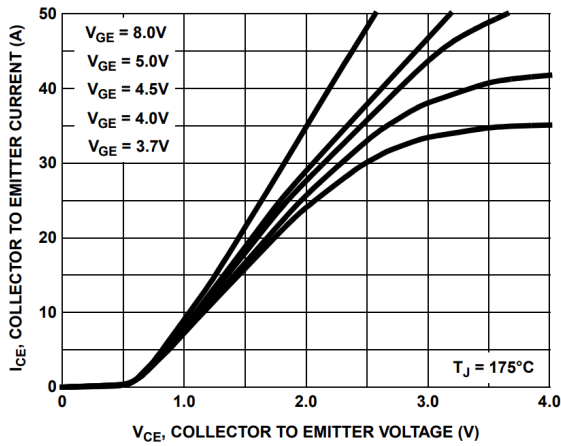


Figure 7. Collector to Emitter On-State Voltage vs. Collector Current

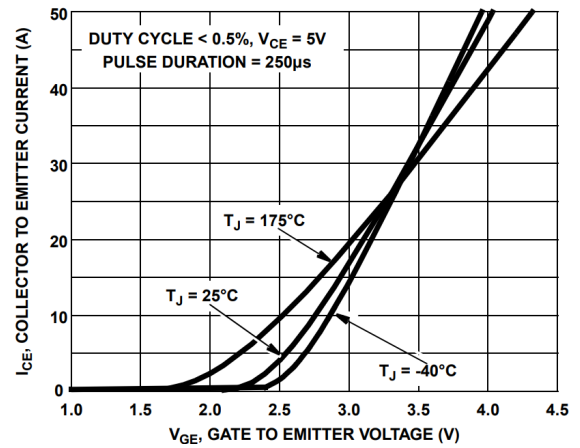


Figure 8. Transfer Characteristics

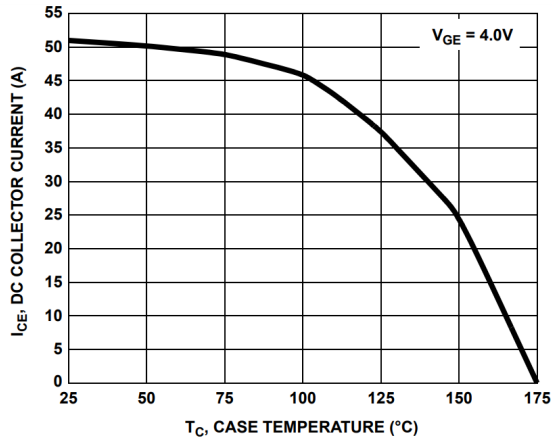


Figure 9. DC Collector Current vs. Case Temperature

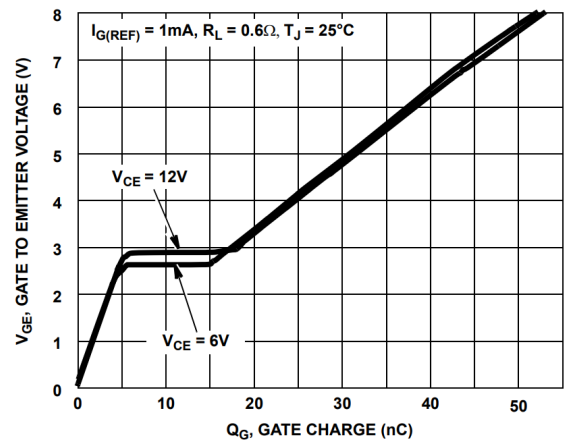


Figure 10. Gate Charge

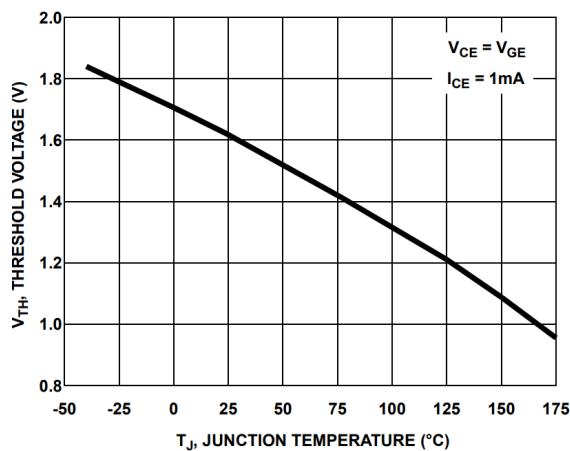


Figure 11. Threshold Voltage vs. Junction Temperature

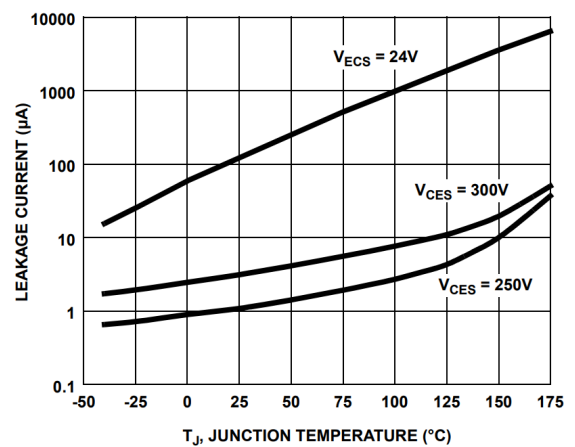


Figure 12. Leakage Current vs. Junction Temperature

TYPICAL CHARACTERISTICS (Continued)

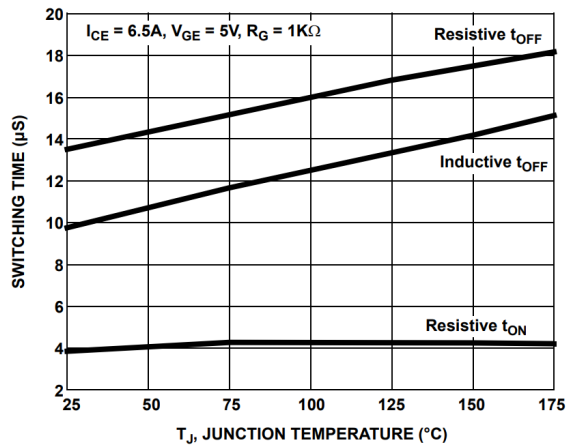


Figure 13. Switching Time vs. Junction Temperature

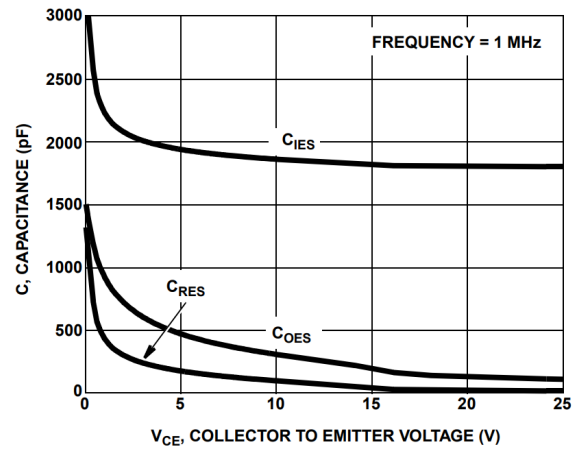


Figure 14. Capacitance vs. Collector to Emitter Voltage

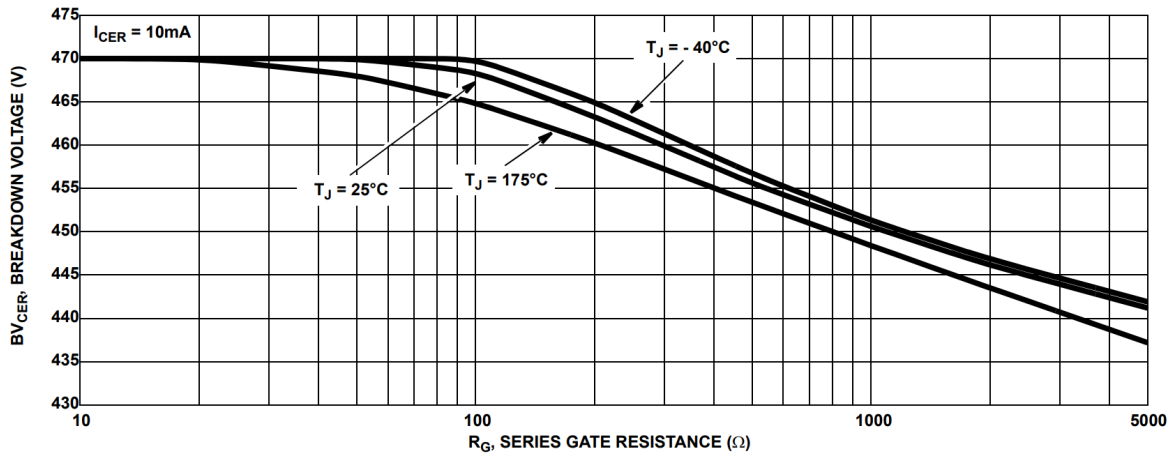


Figure 15. Break down Voltage vs. Series Resistance

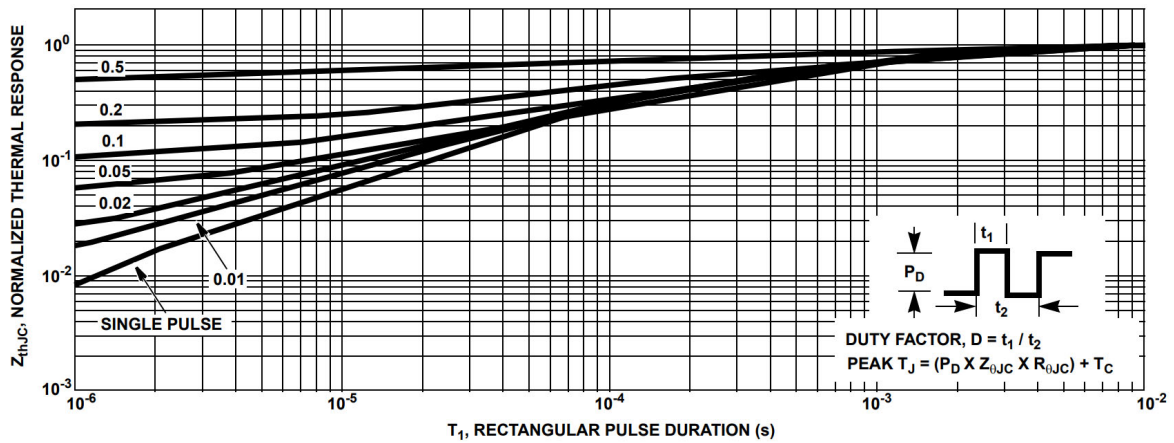


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

TEST CIRCUIT AND WAVEFORMS

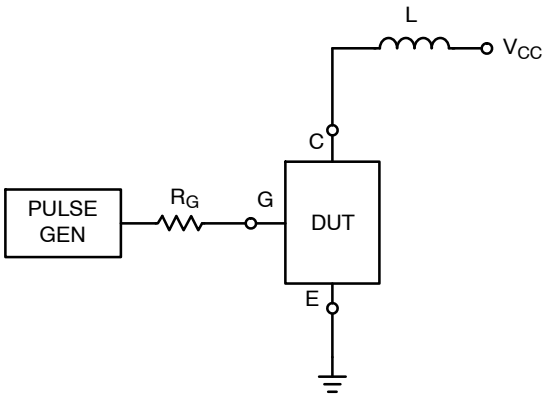


Figure 17. Inductive Switching Test Circuit

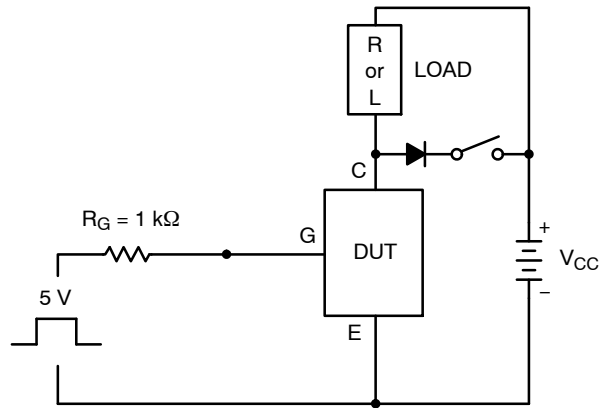


Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

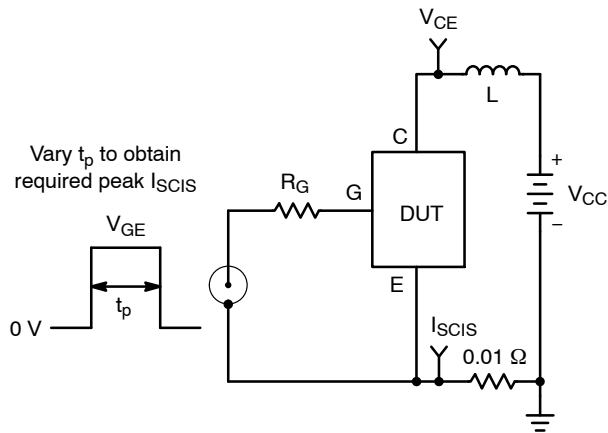


Figure 19. Energy Test Circuit

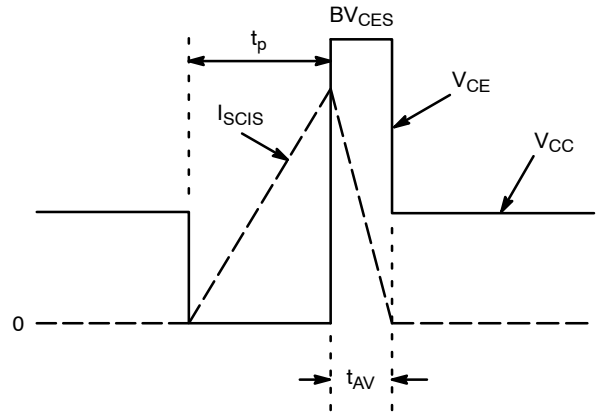
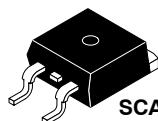


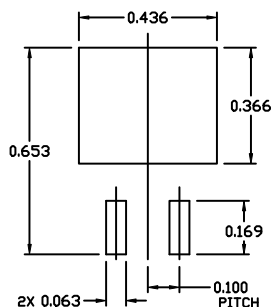
Figure 20. Energy Waveforms



SCALE 1:1

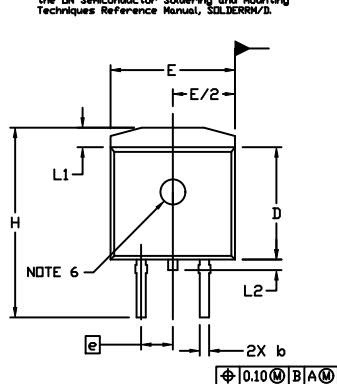
D²PAK-3 (TO-263, 3-LEAD)
CASE 418AJ
ISSUE F

DATE 11 MAR 2021



**RECOMMENDED
MOUNTING FOOTPRINT**

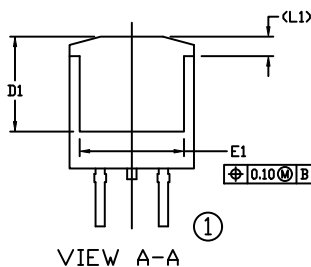
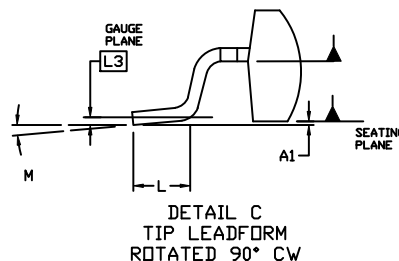
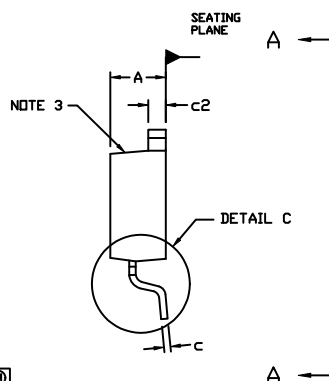
For additional information on our Pb-free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM1.



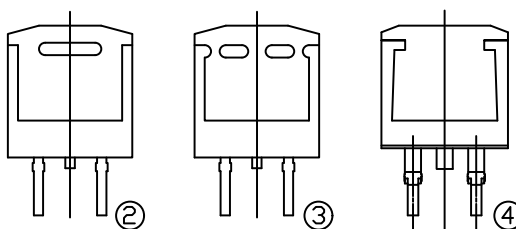
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. CHAMFER OPTIONAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
6. OPTIONAL MOLD FEATURE.
7. ①, ② ... OPTIONAL CONSTRUCTION FEATURE CALL OUTS.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.160	0.190	4.06	4.83
A1	0.000	0.010	0.00	0.25
b	0.020	0.039	0.51	0.99
c	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260	---	6.60	---
E	0.380	0.420	9.65	10.67
E1	0.245	---	6.22	---
e	0.100 BSC	---	2.54 BSC	---
H	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1	---	0.066	---	1.68
L2	---	0.070	---	1.78
L3	0.010 BSC	---	0.25 BSC	---
M	0°	8°	0°	8°

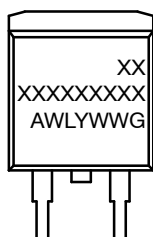


VIEW A-A

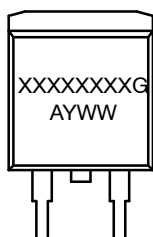


VIEW A-A
OPTIONAL CONSTRUCTIONS

GENERIC MARKING DIAGRAMS*



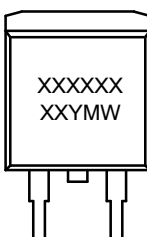
IC



Standard



Rectifier



SSG

XXXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
W = Week Code (SSG)
M = Month Code (SSG)
G = Pb-Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON56370E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	D²PAK-3 (TO-263, 3-LEAD)	PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales